Please amend the present Abstract of the Disclosure as follows.

~~According to the invention, a~~A substrate ~~(2)~~ contained in an enclosure ~~(1)~~ containing an atmosphere ~~(5)~~ that is maintained at low pressure by a device ~~(6, 7)~~ for generating a vacuum is subjected to plasma etching. ~~Plasma generation means~~A plasma generator ~~(8)~~ ~~generate~~ generates a plasma ~~(9)~~ which acts on the surface ~~(2a)~~ of the substrate ~~(2)~~. The etching method subjects the substrate ~~(2)~~ to an alternating succession of steps comprising: an ~~attack~~ etching step using a plasma of etching gas coming from an etching gas source ~~(19)~~, a second step of passivation by means of a plasma of passivation gas coming from a passivation gas source ~~(20)~~, and a pulse step of selective depassivation by the action of a plasma of a cleaning gas coming from a cleaning gas source ~~(21)~~ and serving to remove the polymer from the bottom zones of cavities ~~(2b) more effectively than does the etching gas. This makes it possible to make cavities (2b) having an aspect ratio greater than 30, and to do so at higher speed, with good selectivity relative to the mask protecting the substrate (2).~~